



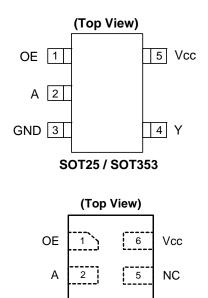
Description

The 74LVC1G126 is a single non-inverting buffer/bus driver with a 3-state output. The output enters a high impedance state when a LOW-level is applied to the output enable (OE) pin. The device is designed for operation with a power supply range of 1.65V to 5.5V. The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using I_{OFF} . The I_{OFF} circuitry disables the output preventing damaging current backflow when the device is powered down.

Features

- Wide Supply Voltage Range from 1.65 to 5.5V
- ± 24mA Output Drive at 3.3V
- CMOS low power consumption
- IOFF Supports Partial-Power-Down Mode Operation
- Inputs accept up to 5.5V
- ESD Protection Tested per JESD 22
 Exceeds 200-V Machine Model (A115-A)
 Exceeds 2000-V Human Body Model (A114-A)
- Latch-Up Exceeds 100mA per JESD 78, Class II
- Range of Package Options
- Direct Interface with TTL Levels
- SOT25, SOT353, and DFN1410: Assembled with "Green" Molding Compound (no Br, Sb)
- Lead Free Finish/ RoHS Compliant (Note 1)

Pin Assignments



DFN1410 (Note 2)

4

Υ

3

Applications

- Voltage Level Shifting
- Bus Driver / Repeater
- Power Down Signal Isolation
- General Purpose Logic
- Wide array of products such as.

GND

- o PCs, networking, notebooks, netbooks, PDAs
- o Computer peripherals, hard drives, CD/DVD ROM
- o TV, DVD, DVR, set top box
- o Cell Phones, Personal Navigation / GPS
- o MP3 players ,Cameras, Video Recorders

Notes: 1. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied. Please visit our website at http://www.diodes.com/products/lead_free.html.

2. Pin 2 and pin 5 of the DFN1410 package are internally connected.

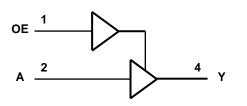


SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Pin Descriptions

Pin Name	Description
OE	Output Enable
А	Data Input
GND	Ground
Y	Data Output
Vcc	Supply Voltage
NC	No Connection

Logic Diagram



Function Table

Inp	Output	
OE	Α	Y
Н	Н	Н
Н	L	L
L	Х	Z



Absolute Maximum Ratings (Note 3)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to 6.5	V
VI	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage applied to output in high impedance or I _{OFF} state	-0.5 to 6.5	V
Vo	Voltage applied to output in high or low state	-0.3 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current VI<0	-50	mA
I _{OK}	Output Clamp Current	-50	mA
lo	Continuous output current	±50	mA
	Continuous current through Vdd or GND	±100	mA
TJ	Operating Junction Temperature	-40 to 150	°C
T _{STG}	Storage Temperature	-65 to 150	°C

Notes: 3. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.



Recommended Operating Conditions (Note 4)

Symbol		Parameter	Min	Мах	Unit	
		Operating	1.65	5.5	V	
V _{CC}	Operating Voltage	Data retention only	1.5	15	V	
		V _{CC} = 1.65V to 1.95V	$0.65 \times V_{CC}$			
N/	High lovel loput Voltage	$V_{CC} = 2.3V$ to 2.7V	1.7		V	
VIH	righ-level input voltage	$V_{CC} = 3V$ to 3.6V	2		v	
		$V_{CC} = 4.5V$ to 5.5V	0.7 X V _{CC}			
		V _{CC} = 1.65V to 1.95V		0.35 X V _{CC}		
		V _{CC} = 2.3V to 2.7V		0.7	v	
VIL		V _{CC} = 3V to 3.6V		0.8	V	
		V _{CC} = 4.5V to 5.5V		0.3 X V _{CC}		
VI	Input Voltage		0	5.5	V	
Vo	Output Voltage		0	V _{CC}	V	
		V _{CC} = 1.65V		-4		
		$V_{CC} = 2.3V$		-8		
I _{OH}	High-level output current	\/		-16	mA	
	IH High-level Input Voltage IL Low-level input voltage $/I$ Input Voltage O Output Voltage OH High-level output current OL Low-level output current ΔV Input transition rise or farate $Operating free-air Operating free-air $	$V_{CC} = 3V$		-24	l	
		$V_{CC} = 4.5V$		-32		
		V _{CC} = 1.65V		4		
		$V_{CC} = 2.3 V$		8		
I _{OL}	Low-level output current	$V_{CC} = 3V$		16	mA	
		VCC = 3V		24		
		$V_{CC} = 4.5V$		32		
		$V_{CC} = 1.8V \pm 0.15V, 2.5V \pm 0.2V$		20		
Δt/ΔV	•	$V_{CC} = 3.3V \pm 0.3V$		10	ns/V	
		$V_{CC} = 5V \pm 0.5V$		5		
T _A	Operating free-air temperature		-40	85	٥C	

Notes: 4. Unused inputs should be held at Vcc or Ground.



Electrical Characteristics (All typical values are at Vcc = 3.3V, T_A = 25° C)

Symbol	Parameter	Test Conditions	Vcc	Min	Тур.	Max	Unit
		I _{OH} = -100μA	1.65V to 5.5V	V _{CC} – 0.1			
		I _{OH} = -4mA	1.65V	1.2			
.,	High Level Output	I _{OH} = -8mA	2.3V	1.9			V
V _{OH}	Voltage	I _{OH} = -16mA	2) (2.4			V
		I _{OH} = -24mA	3V	2.3			
		I _{OH} = -32mA	4.5V	3.8			
		I _{OH} = 100μA	1.65V to 5.5V			0.1	
		I _{OH} = 4mA	1.65V			0.45	
	High-level Input	I _{OH} = 8mA	2.3V			0.3	V
V _{OL}	Voltage	I _{OH} = 16mA	2)/			0.4	V
		I _{OH} = 24mA	3V			0.55	1
		I _{OH} = 32mA	4.5V			0.55	
l _l	Input Current	$V_I = 5.5V$ or GND	0 to 5.5V			± 5	μA
I _{OFF}	Power Down Leakage Current	$V_{\rm I}$ or $V_{\rm O}$ = 5.5V	0			± 10	μA
I _{OZ}	OFF State Leakage Current	$V_0 = 0$ to 5.5V	3.6V			10	μA
Icc	Supply Current	$V_1 = 5.5V$ of GND $I_0 = 0$	1.65V to 5.5V			10	μA
ΔI _{CC}	Additional Supply Current	One input at V_{CC} –0.6V Other inputs at V_{CC} or GND	3V to 5.5V			500	μA
Ci	Input Capacitance	$V_I = V_{CC} - or GND$	3.3		4		pF
	Thermal Desistance	SOT25	(Note 5)		204		°C/W
θ_{JA}	Thermal Resistance Junction-to-Ambient	SOT353	(Note 5)		371		°C/W
		DFN1410	(Note 5)		430		°C/W
	Thermal Resistance	SOT25	(Note 5)		52		°C/W
$\theta_{\rm JC}$	Junction-to-Case	SOT353	(Note 5)		143		°C/W
$ \begin{array}{c} I_{OFF} \\ I_{OZ} \\ I_{CC} \\ \hline C_{i} \\ \theta_{JA} \\ \hline \theta_{IC} \\ \end{array} $		DFN1410	(Note 5)		190		°C/W

Over recommended free-air temperature range (unless otherwise noted)

Notes: 5. Test condition for SOT25, SOT353, and DFN1410: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



Switching Characteristics

	Parameter	From (Input)	TO	Vcc = ± 0.	1.8 V 15V	Vcc = ± 0	2.5 V .2V	Vcc = ± 0	3.3 V .3V		= 5 V 0.5V	Unit
			it) (OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	
	t _{pd}	А	Y	1.7	6.9	0.6	4.6	0.6	3.7	0.5	3.4	ns

Over recommended free-air temperature range, CL = 15pF (see Figure 1)

Over recommended free-air temperature range, CL = 30 or 50pF as noted (see Figure 2)

Parameter	From	TO	Vcc = ± 0.	1.8 V 15V		2.5 V .2V	Vcc = ± 0	3.3 V .3V		= 5 V 0.5V	Unit
	(Input)	(OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pd}	А	Y	2.6	8.0	1.1	5.5	1.0	4.5	1.0	4.0	ns
t _{en}	OE	Y	2.8	9.4	1.3	6.6	1.2	5.3	1.0	4.0	ns
t _{dis}	OE	Y	1.6	9.8	1.0	5.5	1.0	5.5	1.0	4.2	ns

Operating Characteristics

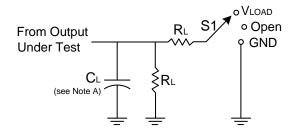
T_A = 25 °C

Parameter		Test Conditions	Vcc = 1.8 V			Vcc = 5 V	Unit	
			Contaitionio	TYP	TYP	TYP	TYP	
	Power	Outputs enabled	f = 10 MHz	19	19	19	21	۶Ē
C _{pd}	dissipation capacitance	Outputs disabled		2	2	3	4	pF



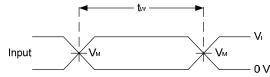
SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Parameter Measurement Information

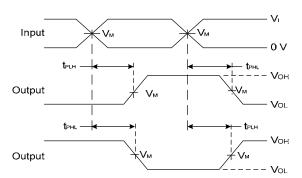


TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	Vload
t _{PHZ} /t _{PZH}	GND

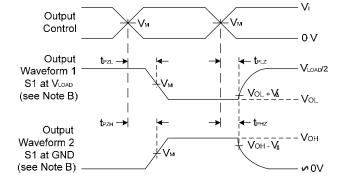
Vcc	Inputs		V _M	V _{LOAD}	CL	RL	V۵	
100	VI	t _r /t _f	• IVI	LUAD	υL	ι.	• A	
1.8V±0.15V	V _{CC}	≤2ns	V _{CC} /2	2 X V _{CC}	15pF	1MΩ	0.15V	
2.5V±0.2V	V _{CC}	≤2ns	V _{CC} /2	2 X V _{CC}	15pF	1MΩ	0.15V	
3.3V±0.3V	3V	≤2.5ns	1.5V	6V	15pF	1MΩ	0.3V	
5V±0.5V	V _{CC}	≤2.5ns	V _{CC} /2	2 X V _{CC}	15pF	1MΩ	0.3V	







Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs



Voltage Waveform Enable and Disable Times Low and High Level Enabling

Figure 1. Load Circuit and Voltage Waveforms

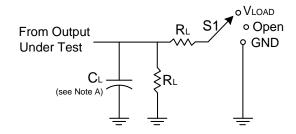
- A. Includes test lead and test apparatus capacitance.
- B. All pulses are supplied at pulse repetition rate \leq 10 MHz.
 - C. Inputs are measured separately one transition per measurement.
 - D. t_{PLZ} and t_{PHZ} are the same as $t_{\mathsf{dis.}}$
 - E. t_{PZL} and t_{PZH} are the same as t_{EN} .
 - F. t_{PLH} and t_{PHL} are the same as $t_{\mathsf{PD.}}$

Notes:



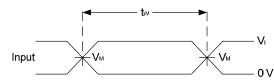
SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Parameter Measurement Information (Continued)

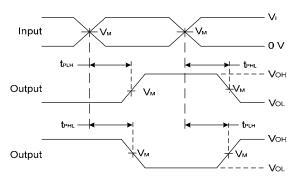


TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	Vload
t _{PHZ} /t _{PZH}	GND

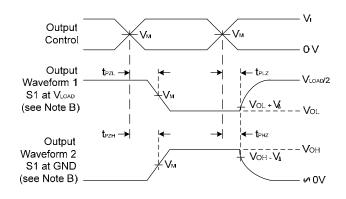
Vcc	Inputs		V _M	V _{LOAD}	CL	RL	VA
	VI	t _r /t _f		FLOAD			• 4
1.8V±0.15V	V _{CC}	≤2ns	V _{CC} /2	2 X V _{CC}	30pF	1KΩ	0.15V
2.5V±0.2V	V _{CC}	≤2ns	V _{CC} /2	2 X V _{CC}	30pF	500Ω	0.15V
3.3V±0.3V	3V	≤2.5ns	1.5V	6V	50pF	500Ω	0.3V
5V±0.5V	V _{CC}	≤2.5ns	V _{CC} /2	$2 X V_{CC}$	50pF	500Ω	0.3V







Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs



Voltage Waveform Enable and Disable Times Low and High Level Enabling

Figure 2. Load Circuit and Voltage Waveforms

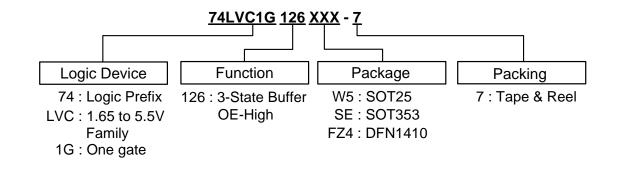
Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied at pulse repetition rate \leq 10 MHz.
- C. Inputs are measured separately one transition per measurement.
- D. t_{PLZ} and t_{PHZ} are the same as $t_{dis.}$
- E. t_{PZL} and t_{PZH} are the same as t_{EN0}
- F. t_{PLH} and t_{PHL} are the same as t_{PD} .



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Ordering Information



	Device	Package Code	Packaging (Note 6)	7" Tape and Reel	
				Quantity	Part Number Suffix
Land-free Green	74LVC1G126W5-7	W5	SOT25	3000/Tape & Reel	-7
	74LVC1G126SE-7	SE	SOT353	3000/Tape & Reel	-7
PD.	74LVC1G126FZ4-7	FZ4	DFN1410	3000/Tape & Reel	-7

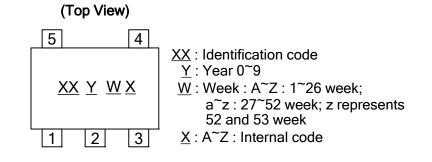
Notes: 6. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Marking Information

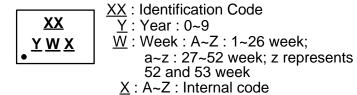
(1) SOT25 and SOT353



Part Number	Package	Identification Code
74LVC1G126W5	SOT25	UZ
74LVC1G126SE	SOT353	UZ

(3) DFN1410

(Top View)



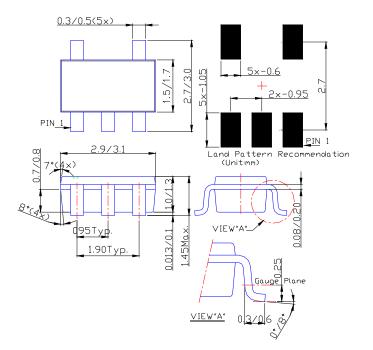
Part Number	Package	Identification Code
74LVC1G126FZ4	DFN1410	UZ



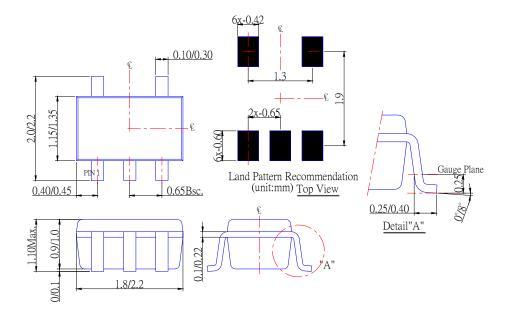
SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Package Outline Dimensions (All Dimensions in mm)

(1) Package Type: SOT25



(2) Package Type: SOT353



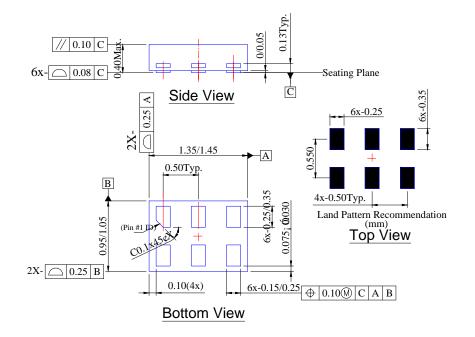
NEW PRODUCT



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Package Outline Dimensions (Continued)

(3) Package Type: DFN1410

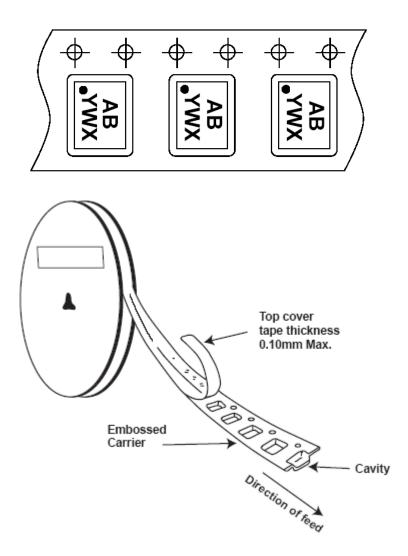


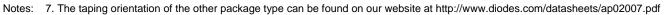


SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Taping Orientation (Note 7)

For DFN1410







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